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20V Dual N-Channel MOSFET



TSSOP-8

Pin Definition:

8 1. Drain 1 8. Drain 2 2. Source 1 7. Source 2 3. Source 1 6. Source 2 4. Gate 1 5. Gate 2

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
20	30 @ V _{GS} = 4.5V	6.0
	40 @ V _{GS} = 2.5V	5.2

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

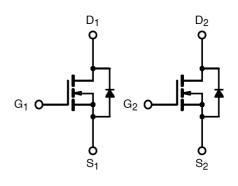
- Specially Designed for Li-on Battery Packs
- Battery Switch Application

Ordering Information

Part No.	Package	Packing
TSM6866SDCA RVG	TSSOP-8	3Kpcs / 13" Reel

Note: "G" denote for Halogen Free Product

Block Diagram



Dual N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	20	V	
Gate-Source Voltage		V_{GS}	±12	V	
Continuous Drain Current		I _D	6	Α	
Pulsed Drain Current		I _{DM}	30	Α	
Continuous Source Current (Diode C	Conduction) ^{a,b}	I _S	1.7	Α	
Maniana Danian Dinainatian	Ta = 25°C	Б	1.6	14/	
Maximum Power Dissipation	Ta = 75°C	$ P_{D}$	1.1	W	
Operating Junction Temperature	·	TJ	+150	°C	
Operating Junction and Storage Ten	perature Range	T _J , T _{STG}	-55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	R⊖ _{JC}	30	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	RO _{JA}	62.5	°C/W

Notes

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, $t \le 5$ sec.



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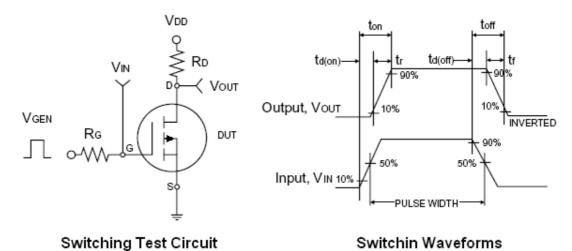


Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static	Static					
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	20	1		V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	0.6	1		V
Gate Body Leakage	$V_{GS} = \pm 12V, V_{DS} = 0V$	I _{GSS}	1	1	±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 20V, V_{GS} = 0V$	I _{DSS}	1	1	1.0	uA
On-State Drain Current	$V_{DS} = 5V, V_{GS} = 4.5V$	I _{D(ON)}	30	-		Α
Drain Course On State Besistance	$V_{GS} = 4.5V, I_D = 6.0A$			21	30	mO.
Drain-Source On-State Resistance	$V_{GS} = 2.5V, I_D = 5.2A$	R _{DS(ON)}	30	40	mΩ	
Forward Transconductance	$V_{DS} = 10V, I_{D} = 6A$	9 _{fs}	1	30		S
Diode Forward Voltage	$I_S = 1.7A, V_{GS} = 0V$	V_{SD}	1	0.7	1.2	V
Dynamic ^b						
Total Gate Charge	- \/ 10\/ GA	Q_g		5	7	
Gate-Source Charge	$V_{DS} = 10V, I_{D} = 6A,$	Q_gs		1		nC
Gate-Drain Charge	$V_{GS} = 4.5V$	Q_{gd}	-	1.5		
Input Capacitance	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	C _{iss}		565		
Output Capacitance	$V_{DS} = 8V, V_{GS} = 0V,$	C _{oss}	1	105		рF
Reverse Transfer Capacitance	f = 1.0MHz	C_{rss}		75		
Switching ^{b,C}						
Turn-On Delay Time		t _{d(on)}	1	8	20	
Turn-On Rise Time	$V_{DD} = 10V, R_L = 10\Omega,$	t _r	1	10	20	0
Turn-Off Delay Time	$I_D = 1A, V_{GEN} = 4.5V,$	t _{d(off)}	-	22	45	nS
Turn-Off Fall Time	$R_G = 6\Omega$	t _f		6	15	

Notes:

- a. pulse test: PW \leq 300 μ S, duty cycle \leq 2%
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.



Document Number: DS_P0000128

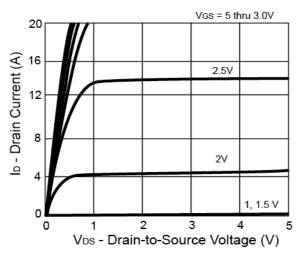


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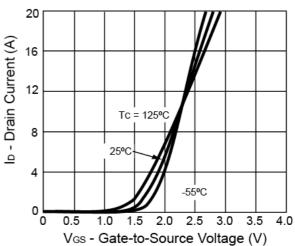


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

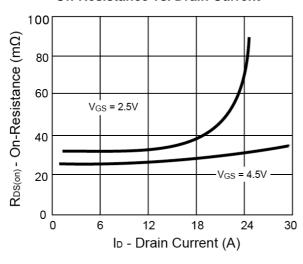
Output Characteristics



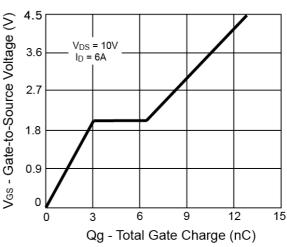
Transfer Characteristics



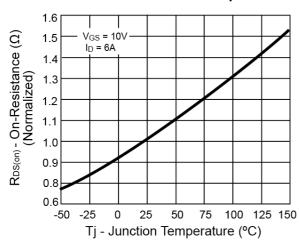
On-Resistance vs. Drain Current



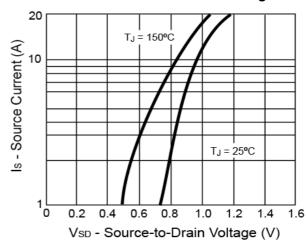
Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



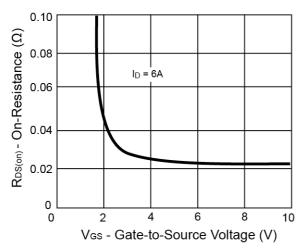


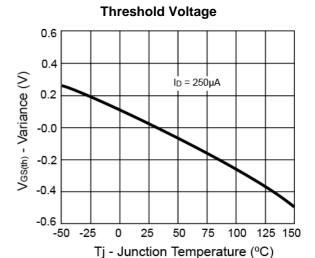
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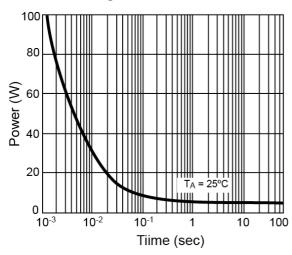
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

On-Resistance vs. Gate-Source Voltage

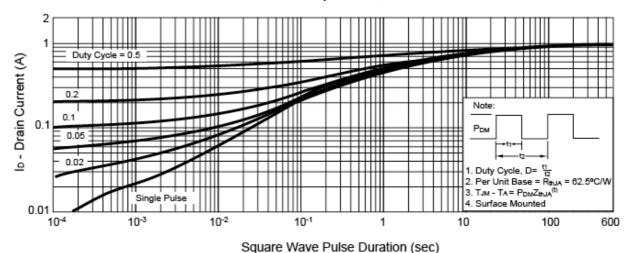




Single Pulse Power



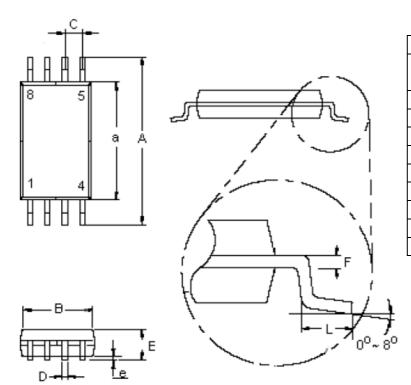
Normalized Thermal Transient Impedance, Junction-to-Ambient



20V Dual N-Channel MOSFET



TSSOP-8 Mechanical Drawing



TSSOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
Α	6.20	6.60	0.244	0.260	
а	4.30	4.50	0.170	0.177	
В	2.90	3.10	0.114	0.122	
С	0.65 (typ)		0.025 (typ)		
D	0.25	0.30	0.010	0.019	
Е	1.05	1.20	0.041	0.049	
е	0.05	0.15	0.002	0.009	
F	0.127		0.005		
L	0.50	0.70	0.020	0.028	

Marking Diagram



Y = Year Code

M = Month Code for Halogen Free Product

5

O =Jan P =Feb Q =Mar R =Apr

 $S = May \quad T = Jun \quad U = Jul \quad V = Aug$

W = Sep X = Oct Y = Nov Z = Dec

L = Lot Code



TSM6866SD 20V Dual N-Channel MOSFET

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